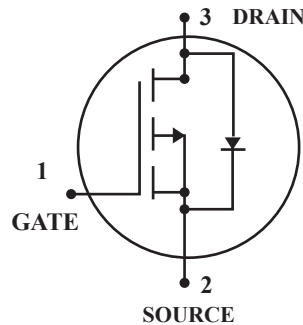


## P-Channel Enhancement Mode Power MOSFET

 Lead(Pb)-Free

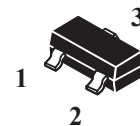


**DRAIN CURRENT**  
-1.9 AMPERES

**DRAIN SOURCE VOLTAGE**  
-30 VOLTAGE

### Features:

- \*Super High Dense Cell Design For Low  $R_{DS(ON)}$   
 $R_{DS(ON)} < 240m\Omega @ V_{GS} = -10V$
- \*Rugged and Reliable
- \*Simple Drive Requirement
- \*SOT-23 Package



**SOT-23**

### Applications

- \*Power Management in Notebook Computer
- \*Portable Equipment
- \*Battery Powered System

### Maximum Ratings ( $T_A = 25^\circ C$ Unless Otherwise Specified)

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>3</sup> , ( $T_A = 25^\circ C$ ) $I_D$ ( $T_A = 70^\circ C$ )	$I_D$	-1.9	A
		-1.5	
Pulsed Drain Current <sup>1,2</sup>	$I_{DM}$	-10	
Total Power Dissipation ( $T_A = 25^\circ C$ )	$P_D$	1.38	W
Maximum Thermal Resistance Junction-ambient <sup>3</sup>	$R_{\theta JA}$	90	$^\circ C/W$
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	$^\circ C$

### Device Marking

WTC2303=2303

## Electrical Characteristics ( $T_A = 25^\circ\text{C}$ Unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### Static

Drain-Source Breakdown Voltage $V_{GS}=0, I_D=-250\mu\text{A}$	$V_{(BR)DSS}$	-30	-	-	V
Gate-Source Threshold Voltage $V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	$V_{GS(Th)}$	-1.0	-	-	
Gate-Source Leakage Current $V_{GS} = \pm 20\text{V}$	$I_{GSS}$	-	-	$\pm 100$	nA
Drain- Source Leakage Current( $T_j=25^\circ\text{C}$ ) $V_{DS}=-30\text{V}, V_{GS}=0$	$I_{DSS}$	-	-	-1	$\mu\text{A}$
Drain- Source Leakage Current( $T_j=70^\circ\text{C}$ ) $V_{DS}=-30\text{V}, V_{GS}=0$		-	-	-10	
Drain-Source On-Resistance <sup>2</sup> $V_{GS}=-10\text{V}, I_D=-1.7\text{A}$ $V_{GS}=-4.5\text{V}, I_D=-1.3\text{A}$	$R_{DS(on)}$	-	-	240 460	$\text{m}\Omega$
Forward Transconductance $V_{DS}=-10\text{V}, I_D=-1.7\text{A}$	$g_{fs}$	-	2	-	S

### Dynamic

Input Capacitance $V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1.0\text{MHz}$	$C_{iss}$	-	230	-	pF
Output Capacitance $V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1.0\text{MHz}$	$C_{oss}$	-	130.4	-	
Reverse Transfer Capacitance $V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1.0\text{MHz}$	$C_{rss}$	-	40	-	

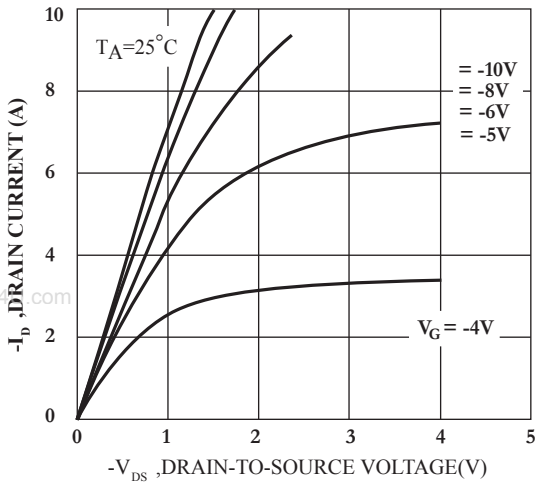
## Switching

Turn-on Delay Time <sup>2</sup> $V_{DS}=-15V, V_{GS}=-10V, I_D=-1A, R_D=15\Omega, R_G=6\Omega$	$t_{d(on)}$	-	7.6	-	ns
Rise Time $V_{DS}=-15V, V_{GS}=-10V, I_D=-1A, R_D=15\Omega, R_G=6\Omega$	$t_r$	-	8.2	-	
Turn-off Delay Time $V_{DS}=-15V, V_{GS}=-10V, I_D=-1A, R_D=15\Omega, R_G=6\Omega$	$t_{d(off)}$	-	17.5	-	
Fall Time $V_{DS}=-15V, V_{GS}=-10V, I_D=-1A, R_D=15\Omega, R_G=6\Omega$	$t_f$	-	9	-	
Total Gate Charge <sup>2</sup> $V_{DS}=-15V, V_{GS}=-10V, I_D=-1.7A$	$Q_g$	-	6.2	10	nC
Gate-Source Charge $V_{DS}=-15V, V_{GS}=-10V, I_D=-1.7A$	$Q_{gs}$	-	1.4	-	
Gate-Drain Change $V_{DS}=-15V, V_{GS}=-10V, I_D=-1.7A$	$Q_{gd}$	-	0.3	-	

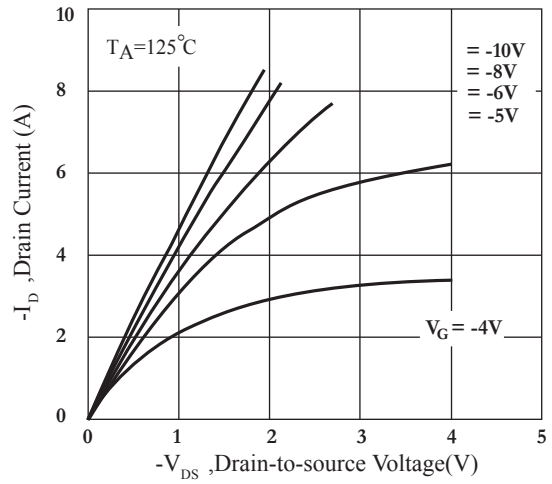
## Source-Drain Diode Characteristics

Forward On Voltage <sup>2</sup> $V_{GS}=0V, I_S=-1.25A @T_j=25^\circ C$	$V_{SD}$	-	-	-1.2	V
Continuous Source Current(Body Diode) $V_D=V_G=0V, V_S=-1.2V$	$I_S$	-	-	-1	A
Pulsed Source Current(Body Diode) <sup>1</sup>	$I_{SM}$	-	-	-10	A

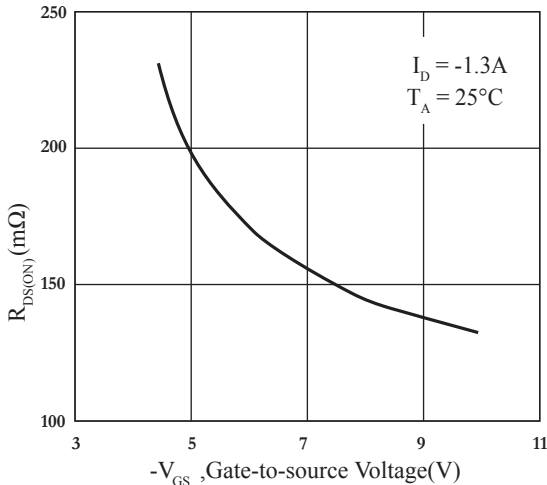
- Note: 1. Pulse width limited by Max, junction temperature.  
 2. pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .  
 3. Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board; 270°C/W when mounted on min, copper pad.



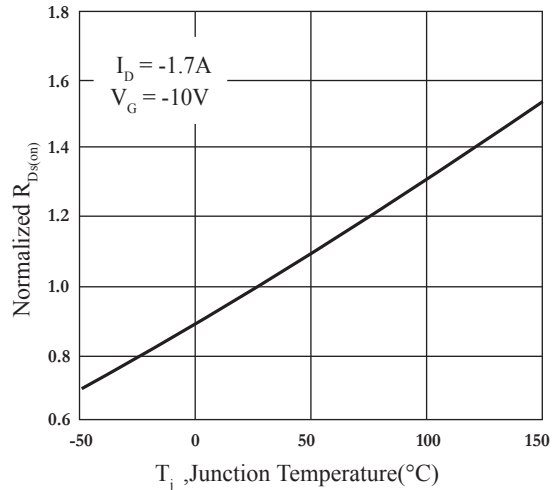
**FIG.1 Typical Output Characteristics**



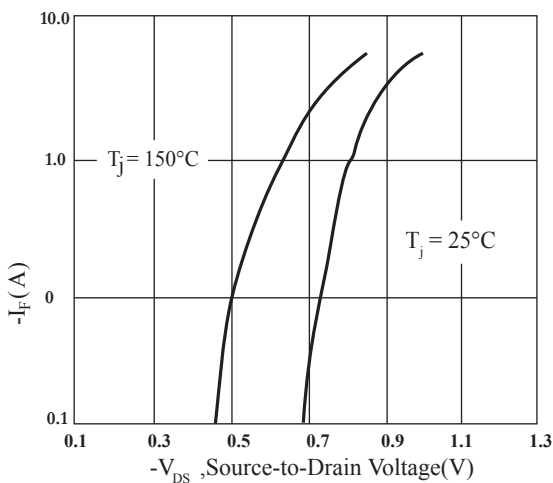
**Fig.2 Typical Output Characteristics**



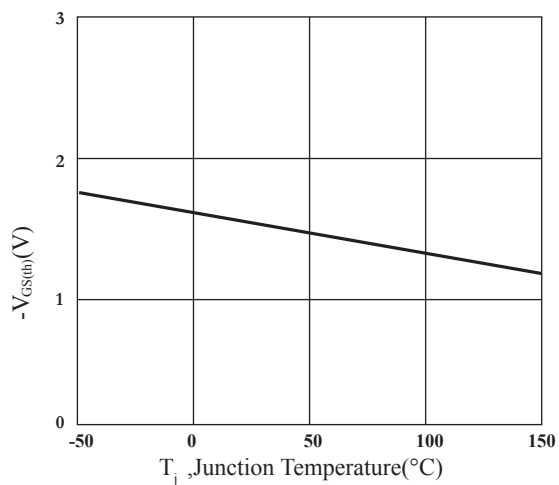
**FIG.3 On-Resistance v.s. Gate Voltage**



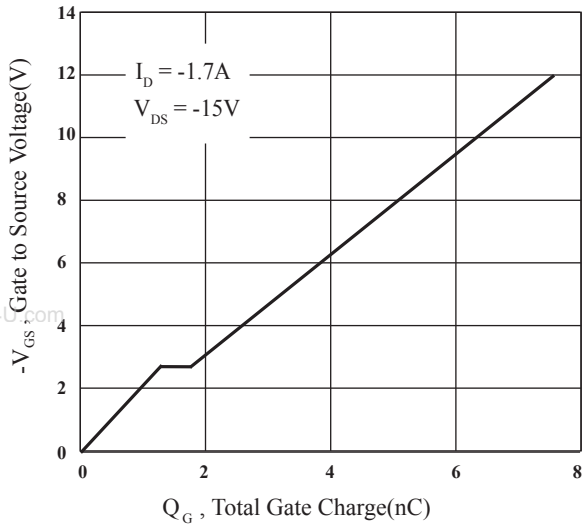
**Fig.4 Normalized On-Resistance**



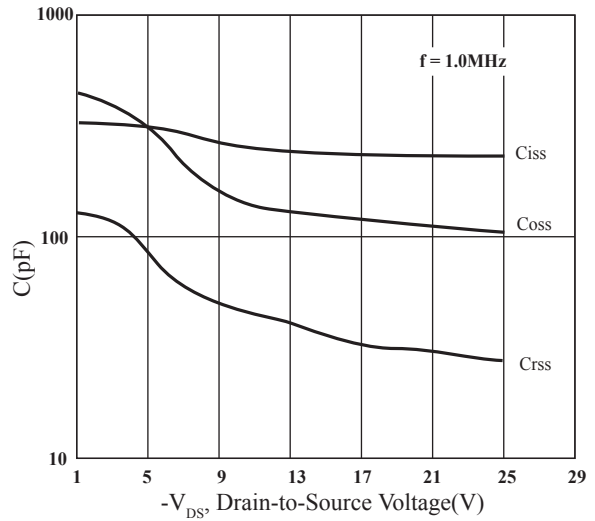
**Fig.5 Forward Characteristics of Reverse Diode**



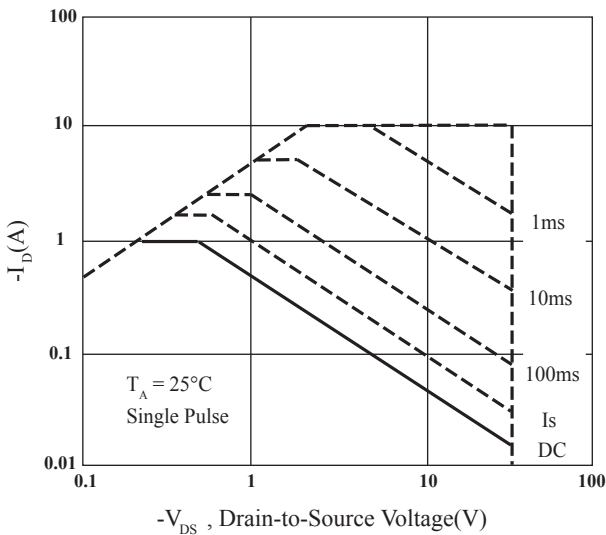
**Fig.6 Gate Threshold Voltage v.s. Junction Temperature**



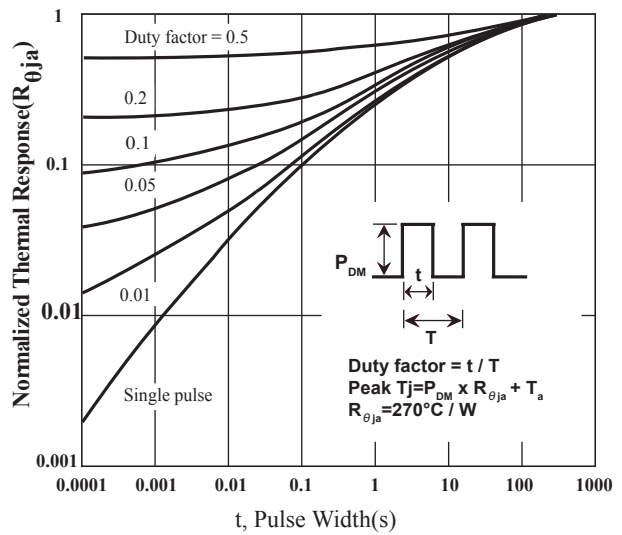
**Fig 7. Gate Charge Characteristics**



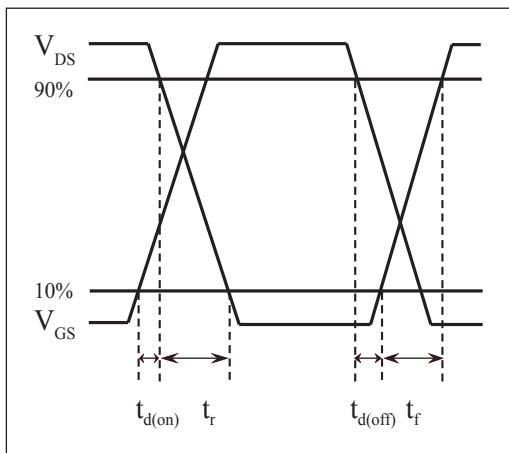
**Fig 8. Typical Capacitance Characteristics**



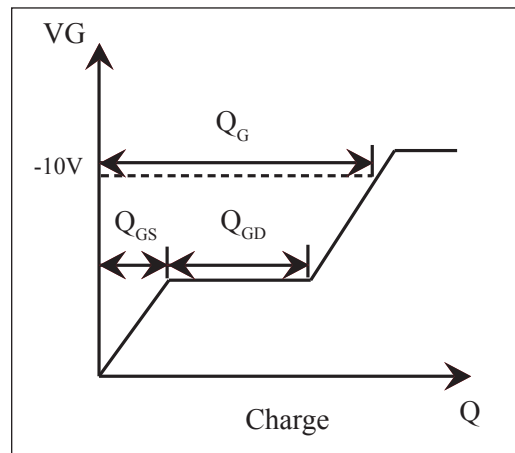
**Fig 9. Maximum Safe Operation Area**



**Fig 10. Effective Transient Thermal Impedance**

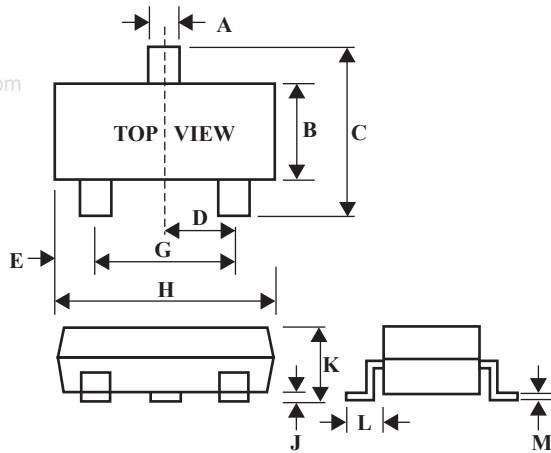


**Fig 11. Switching Time Waveform**



**Fig 12. Gate Charge Waveform**

### SOT-23 Outline Dimension



SOT-23		
Dim	Min	Max
A	0.35	0.51
B	1.19	1.40
C	2.10	3.00
D	0.85	1.05
E	0.46	1.00
G	1.70	2.10
H	2.70	3.10
J	0.01	0.13
K	0.89	1.10
L	0.30	0.61
M	0.076	0.25